L Numb r	Hits	Search Text	DB	Time stamp
-	0	476526.apn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 11:13
-	1	6547937.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 14:25
-	152	204/$.ccls. and (cleaning adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/28 16:24
-	17	(204/$.ccls. and (cleaning adj electrode)) and (microelectronic or wafer or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/28 16:24
-	12396	204/$.ccls. and (anode same cathode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 10:53
-	1	782216.apn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:12
-	59395	204/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:12
-	35240	205/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:13
-	83968	204/$.ccls. 205/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:13
-	10782	(204/$.ccls. 205/$.ccls.) and (microelectronic or semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:13
-	1310	((204/$.ccls. 205/$.ccls.) and (microelectronic or semiconductor or wafer)) and ((second or secondary or another or additional) near (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:14
-	574	((204/$.ccls. 205/$.ccls.) and (microelectronic or semiconductor or wafer)) and ((clean$5 or strip$5 deposit) near2 (anode or cathode or electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:18

-		174	(((204/$.ccls. 205/$.ccls.) and (micro l ctronic or semiconductor or wafer)) and ((s cond or secondary or another or additional) near (el ctrod or cathode or anode))) and (((204/$.ccls. 205/$.ccls.) and (micro l ctronic or semiconductor or wafer)) and ((clean$5 or strip$5 d posit) near2 (anode or cathode or electrode)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:18
-		93	(((((204/$.ccls. 205/$.ccls.) and (microelectronic or semiconductor or wafer)) and ((second or secondary or another or additional) near (electrode or cathode or anode))) and (((204/$.ccls. 205/$.ccls.) and (microelectronic or semiconductor or wafer)) and ((clean$5 or strip$5 deposit) near2 (anode or cathode or electrode)))) and (etch$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:18
-		462	205/640,646,648,652,686.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 14:26
-		98	205/640,646,648,652,686.ccls. and clean$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:10
-		744	204/224m.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:10
-		2427	204/275.1,237,242,280.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/30 15:02
-		3092	204/224m.ccls. 204/275.1,237,242,280.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:10
-		167	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and ((electrochem$7 or electrol$7 or (electro adj chem$7)) near2 (etch$5 or polish$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:12
-		100	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and (electropolish$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:12
-		57	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and ((electropolish$5) with (electrode or anode or cathode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:13
-		87	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and (((electrochem$7 or electrol$7 or (electro adj chem$7)) near2 (etch$5 or polish$3)) with (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:21
-		809	(204/$.ccls. 205/$.ccls.) and ((((builld or built) adj up) or d posit$5 or collect$3) with (electrode or cathod or electrode) with (distance or gap or spacing))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:23

-	179	(204/$.ccls. 205/$.ccls.) and (((((builld or built) adj up) or deposit$5 or collect$3) with (electrode or cathode or el ctrode) with (distanc or gap or spacing)) same (remov$4 or cl an$3 or strip$4 or etch$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:25
-	804	(204/$.ccls. 205/$.ccls.) and (((((builld or built) adj up) or deposit$5 or collect$3) with (electrode or cathode or electrode) with (distance or gap or spacing)) same ((remov$4 or clean$3 or strip$4 or etch$4) with ((builld or built) adj up) or deposit$5 or collect$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:28
-	133	(204/$.ccls. 205/$.ccls.) and (((((builld or built) adj up) or deposit$5 or collect$3) with (electrode or cathode or electrode) with (distance or gap or spacing)) same ((remov$4 or clean$3 or strip$4 or etch$4) with (((builld or built) adj up) or deposit$5 or collect$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:29
-	3	(("6500324") or ("6174425")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:33
-	8867	204/$.ccls. and (microelectronic or semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 10:30
-	2347	(204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 10:31
-	1056	(204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 13:15
-	65	((204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (mesh with anode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 13:17
-	75	((204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (mesh with (anode or porous))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:14
-	160	((204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrod) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passag or passageway or flow or opening or inlet or outlet))) and (anode with (m sh or porous))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:15

-		110	((204/$.ccls. and (microel ctronic or semiconductor or waf r)) and ((anod or cathode or electrod) with (fluid or solution or lectrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inl t or outl t))) and (anode with rotat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:15
-		125	((204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat$5 or mov$7))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:16
-		60	(((204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat$5 or mov$7))) and (((204/$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode with (mesh or porous)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:23
-		2	6197182.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:35
-		1349	204/$.ccls. and (solution with ((rins$4 or clean$5) and (electroplat$5 or electroly$6 or plating)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:39
-		765	(204/$.ccls. and (solution with ((rins$4 or clean$5) and (electroplat$5 or electroly$6 or plating)))) not rinsed!	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:40
-		3	((("6103096") or ("5614076") or ("5531874") or ("5486282") or ("5543032") or ("5536388") or ("5567300") or ("5284554")).PN.) and ((rins$ or clean$) with (plating or electroly$5 or electroplat$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:43
-		5	6103096.URPN.	USPAT	2003/07/30 14:44
-		15	(("6103096") or ("5614076") or ("5531874") or ("5486282") or ("5543032") or ("5536388") or ("5567300") or ("5284554")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:49
-		29	5567300.URPN.	USPAT	2003/07/30 14:47

-	20	5543032.URPN.	USPAT	2003/07/30 14:48
-	6	5536388.URPN.	USPAT	2003/07/30 14:48
-	15	5486282.URPN.	USPAT	2003/07/30 14:48
-	19	5284554.URPN.	USPAT	2003/07/30 14:48
-	62	5567300.URPN. 5543032.URPN. 5536388.URPN. 5486282.URPN. 5284554.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:49
-	0	(5567300.URPN. 5543032.URPN. 5536388.URPN. 5486282.URPN. 5284554.URPN.) and (clean$5 with (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:50
-	26	(5567300.URPN. 5543032.URPN. 5536388.URPN. 5486282.URPN. 5284554.URPN.) and (remov$5 with (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:55
-	83968	204/$.ccls. 205/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:56
-	3	(204/$.ccls. 205/$.ccls.) and (electrochem$7 near (micromachin$5 or machin$5)) and (clean$ near (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:57
-	295	204/275.1,237,242,280.ccls. and (titanium with (platinum or platinized))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/30 15:05
-	83	(204/275.1,237,242,280.ccls. and (titanium with (platinum or platinized))) and (microelectronic or semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/30 15:06